

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device comprising:

a thick film wiring having a first film thickness;

a thin film wiring having a second film thickness that is smaller than the first film

thickness, said thick film wiring and said thin film wiring being formed in a single layer; and

a hard mask covering only the surface of said thick film therewith;

wherein said hard mask is resistant to etching adapted for patterning of said thick film wiring and also to etching adapted for patterning of said thin film wiring, while being resistant to heat.

2. (Original) The semiconductor device according to Claim 1, wherein said hard mask comprises a silicon oxide film.

3. (Original) The semiconductor device according to Claim 1, wherein said hard mask comprises a silicon nitride film.

4. (Original) The semiconductor device according to Claim 1, wherein said hard mask comprises a tungsten film.

5. (Currently Amended) ~~[[The]]~~ A semiconductor device ~~according to Claim 1~~
comprising:

a thick film wiring having a first film thickness;

a thin film wiring having a second film thickness that is smaller than the first film thickness, said thick film wiring and said thin film wiring being formed in a single layer; and
a hard mask covering the surface of said thick film therewith;
wherein said hard mask is resistant to etching adapted for patterning of said thick film wiring and also to etching adapted for patterning of said thin film wiring, while being resistant to heat, wherein

said thick film wiring serves as a wiring for an electric supply of said semiconductor device or as a wiring for ground.

6. (Withdrawn) A semiconductor device comprising:

a thick film wiring having a first film thickness;
a thin film wiring having a second film thickness smaller than said first film thickness,
said thick film wiring and said thin film wiring being formed in a single layer; and
a metallic anti-reflective film covering the surface of said thin film wiring.

7. (Withdrawn) The semiconductor device according to Claim 6, wherein said thick film wiring has a flattened portion having a film thickness equal to said thin film wiring, and a protruded portion formed on said flattened portion, said protruded portion having such a layout that an occupying area thereof is smaller than that of said flattened portion.

8. (Withdrawn) The semiconductor device according to Claim 7, wherein a boundary between said flattened portion and said protruded portion is constituted of a single metal material, and a metallic anti-reflective film is provided to cover the surface of said thick film wiring.

9. (Withdrawn) The semiconductor device according to Claim 7, wherein a metallic anti-reflective film is interposed at the boundary between said flattened portion and said protruded portion to cover the entire surface of said flattened portion therewith.

10. (Withdrawn) The semiconductor device according to Claim 6, wherein said thick film wiring serves as a wiring for an electric supply of said semiconductor device or as a wiring for ground.

11. (Withdrawn) A semiconductor device comprising:
a thick film wiring having a first film thickness;
a thin film wiring having a second film thickness smaller said first film thickness, said thick film wiring and said thin film wiring being formed in a single layer; and
an inter-layer insulating film surrounding said thick film wiring and covering said thin film wiring;
wherein said thick film wiring also serves as a plug which functions as a plug capable of connection with a wiring layer formed as an upper layer on said inter-layer insulating film.

12. (Withdrawn) The semiconductor device according to Claim 11, further comprising a metallic anti-reflective film covering a surface of said thin film wiring.

13. (Withdrawn) The semiconductor device according to Claim 12, further comprising a metallic anti-reflective film covering a side surface of said thick film wiring for plug.

14. (Withdrawn) The semiconductor device according to Claim 13, wherein:

said thin film wiring includes a portion formed adjacently to said thick film wiring for

plug;

said anti-reflective film formed on the surface of the portion of said thin film wiring and said anti-reflective film covering the side surfaces of said thick film wiring for plug form a continuous film.

15. (Withdrawn) The semiconductor device according to Claim 12, wherein said thick film wiring for plug comprises:

a metal film base portion having the same film thickness and kind of material as said thin film wiring;

a metallic anti-reflective film covering the surface of said base portion; and

a second metal film portion formed on said anti-reflective film.

16. (Withdrawn) The semiconductor device according to Claim 15, wherein:

said thin film wiring includes a portion formed adjacently to said thick film wiring for plug;

said anti-reflective film interposed between said base metal portion and said second metal portion of said thick film wiring for plug and said anti-reflective film covering the side surfaces of said thick film wiring for plug form a continuous film.

17. (Previously Presented) A semiconductor device according to claim 1, wherein the

hard mask is resistant to heat at 400°C.
